

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE****Applicant(s):** Tze-chiang Chen, et al.**Examiner:** C.Q. Nguyen**Serial No:** 10/700,085**Art Unit:** 2811**Filed:** November 3, 2003**Docket:** YOR920030586US1 (17201)**Dated:** December 14, 2004**For:** METHOD FOR FABRICATING SiGe-ON-INSULATOR (SGOI) AND  
Ge-ON-INSULATOR (GOI) SUBSTRATES**Confirmation No.** 2805Commissioner for Patents  
United States Patent and Trademark Office  
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DEC 14 2004**RESPONSE UNDER 37 C.F.R. §§1.111 AND 1.143**

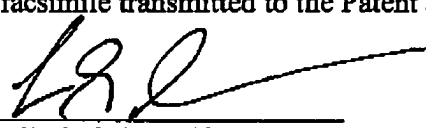
Sir:

In response to the Office Action dated December 2, 2004, applicants provisionally elect, without traverse, the subject matter of Embodiment 1 described in FIG. 1, for continued prosecution in the above-identified patent application.

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**CERTIFICATION OF FACSIMILE TRANSMISSION**

I hereby certify that this paper is being facsimile transmitted to the Patent and Trademark Office on the date shown below.

**Dated:** December 14, 2004  
Leslie S. Szivos, Ph.D.